

UNITED STATES PATENT AND TRADEMARK OFFICE  
**CERTIFICATE OF CORRECTION**

PATENT NO. : 6,936,484 B2  
DATED : August 30, 2005  
INVENTOR(S) : Masakazu Kanechika et al.

Page 1 of 1

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

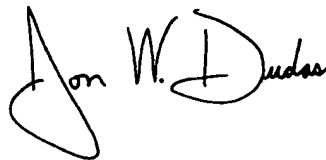
Column 46,

Line 20, Claim 16 should read:

-- A method as defined in claim 15, wherein the semiconductor material substrate or layer comprises silicon; the first impurity is oxygen; and the second impurity is boron. --.

Signed and Sealed this

Third Day of January, 2006

A handwritten signature in black ink, appearing to read "Jon W. Dudas". The signature is stylized with a large, looped initial "J" and a distinct "D" at the end.

JON W. DUDAS  
*Director of the United States Patent and Trademark Office*